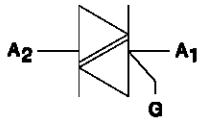
SGS-THOMSON MICROELECTRONICS

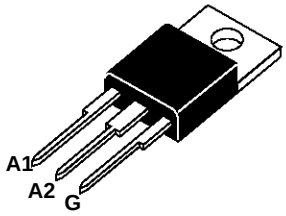
BTA08 S/A
BTB08 S/A

SENSITIVE GATE TRIACS

FEATURES

- VERY LOW I_{GT} = 10mA max
- LOW I_H = 25mA max
- BTA Family :
  INSULATING VOLTAGE = 2500$V_{(RMS)}$
  (UL RECOGNIZED : E81734)





TO220AB
(Plastic)

DESCRIPTION

The BTA/BTB08 S/A triac family are high performance glass passivated PNPN devices.
These parts are suitables for general purpose applications where gate high sensitivity is required. Application on 4Q such as phase control and static switching.

ABSOLUTE RATINGS (limiting values)

Symbol	Parameter			Value	Unit
$I_{T(RMS)}$	RMS on-state current (360° conduction angle)	BTA	Tc = 75°C	8	A
		BTB	Tc = 80°C		
I_{TSM}	Non repetitive surge peak on-state current (Tj initial = 25°C)		tp = 8.3 ms	84	A
			tp = 10 ms	80	
I^2t	I^2t value		tp = 10 ms	32	A^2s
dI/dt	Critical rate of rise of on-state current Gate supply : I_G = 50mA di_G/dt = 0.1A/µs		Repetitive F = 50 Hz	10	A/µs
			Non Repetitive	50	
Tstg Tj	Storage and operating junction temperature range			- 40 to + 150 - 40 to + 110	°C °C
Tl	Maximum lead temperature for soldering during 10 s at 4.5 mm from case			260	°C

Symbol	Parameter	BTA / BTB08-			Unit
		400 S/A	600 S/A	700 S/A	
V_{DRM} V_{RRM}	Repetitive peak off-state voltage Tj = 110°C	400	600	700	V

THERMAL RESISTANCES

Symbol	Parameter		Value	Unit
Rth (j-a)	Junction to ambient		60	°C/W
Rth (j-c) DC	Junction to case for DC	BTA	4.4	°C/W
		BTB	3.2	
Rth (j-c) AC	Junction to case for 360° conduction angle (F= 50 Hz)	BTA	3.3	°C/W
		BTB	2.4	

GATE CHARACTERISTICS (maximum values)

$P_{G\ (AV)}$ = 1W P_{GM} = 10W (tp = 20 µs) I_{GM} = 4A (tp = 20 µs) V_{GM} = 16V (tp = 20 µs).

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions		Quadrant		Suffix		Unit
					S	A	
I_{GT}	V_D=12V (DC) R_L=33Ω	Tj=25°C	I-II-III	MAX	10	10	mA
			IV	MAX	10	25	
V_{GT}	V_D=12V (DC) R_L=33Ω	Tj=25°C	I-II-III-IV	MAX	1.5		V
V_{GD}	V_D=V_{DRM} R_L=3.3kΩ	Tj=110°C	I-II-III-IV	MIN	0.2		V
tgt	V_D=V_{DRM} I_G = 40mA dI_G/dt = 0.5A/µs	Tj=25°C	I-II-III-IV	TYP	2		µs
I_L	IG= 1.2 I_{GT}	Tj=25°C	I-III-IV	TYP	20	20	mA
			II		40	40	
I_H *	I_T= 100mA gate open	Tj=25°C		MAX	25	25	mA
V_{TM} *	I_{TM}= 11A tp= 380µs	Tj=25°C		MAX	1.75		V
I_{DRM} I_{RRM}	V_{DRM} Rated V_{RRM} Rated	Tj=25°C		MAX	0.01		mA
		Tj=110°C		MAX	0.75		
dV/dt *	Linear slope up to V_D=67%V_{DRM} gate open	Tj=110°C		MIN	10	10	V/µs
(dV/dt)c *	(dI/dt)c= 3.5A/ms	Tj=110°C		TYP	5	5	V/µs

* For either polarity of electrode A_2 voltage with reference to electrode A_1.

ORDERING INFORMATION

Package	$I_{T(RMS)}$	V_{DRM} / V_{RRM}	Sensitivity Specification	
	A	V	S	A
BTA (Insulated)	8	400	X	X
		600	X	X
		700	X	X
BTB (Uninsulated)		400	X	X
		600	X	X
		700	X	X

Fig.1 : Maximum RMS power dissipation versus RMS on-state current (F=50Hz).
(curves are cut off by (dI/dt)c limitation)

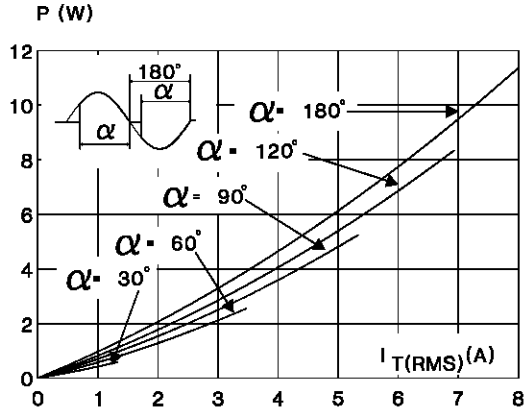


Fig.2 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTA).

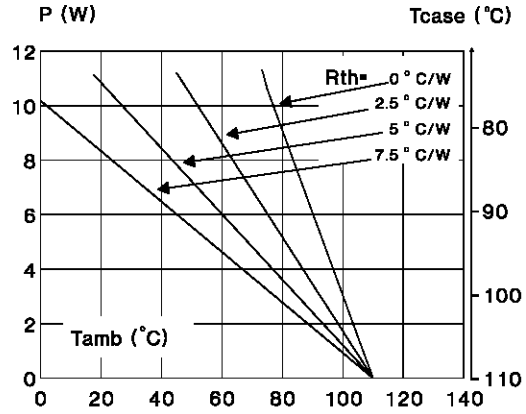


Fig.3 : Correlation between maximum RMS power dissipation and maximum allowable temperatures (T_{amb} and T_{case}) for different thermal resistances heatsink + contact (BTB).

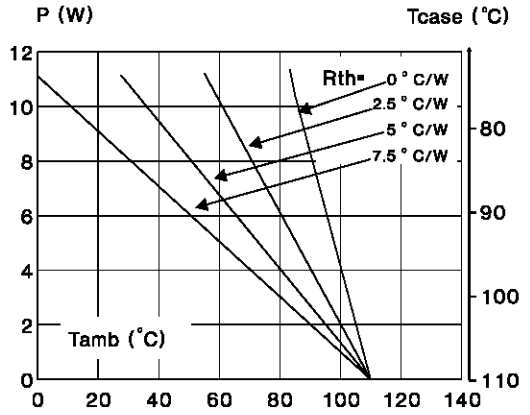


Fig.4 : RMS on-state current versus case temperature.

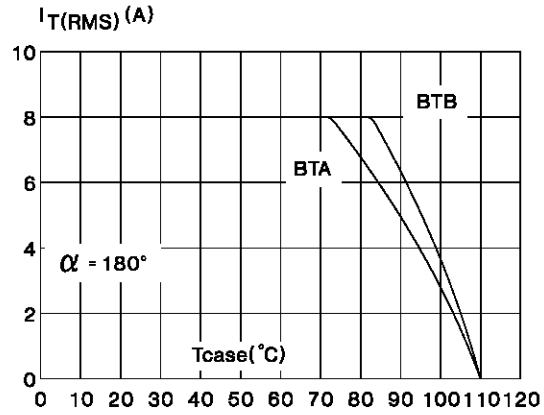


Fig.5 : Relative variation of thermal impedance versus pulse duration.

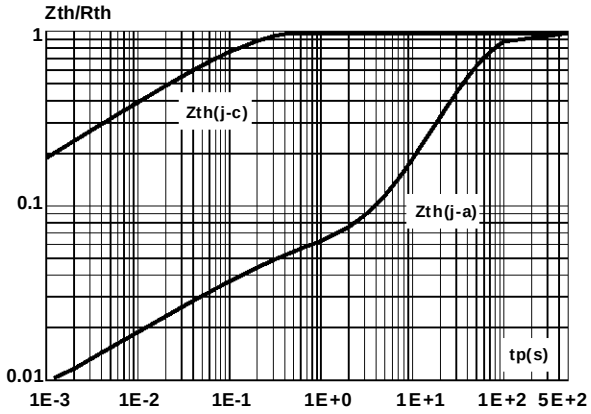


Fig.6 : Relative variation of gate trigger current and holding current versus junction temperature.

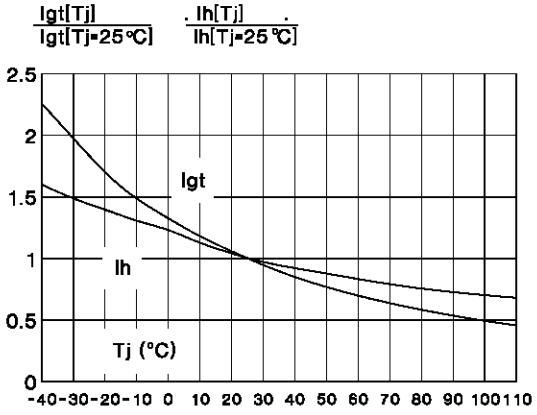


Fig.7 : Non Repetitive surge peak on-state current versus number of cycles.

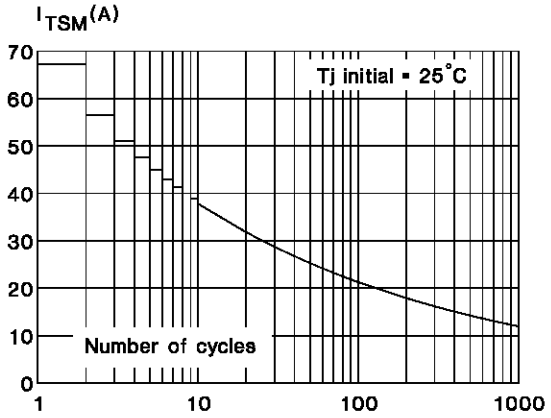


Fig.8 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : t ≤ 10ms, and corresponding value of I^2t.

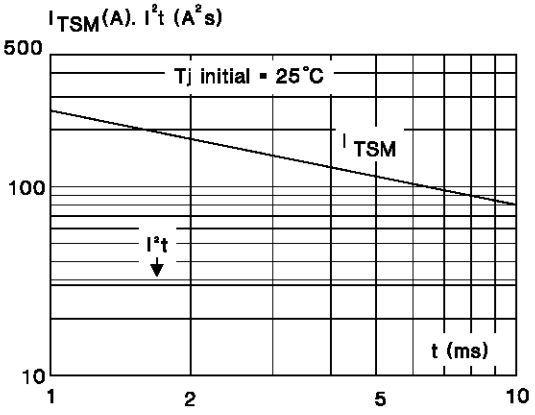
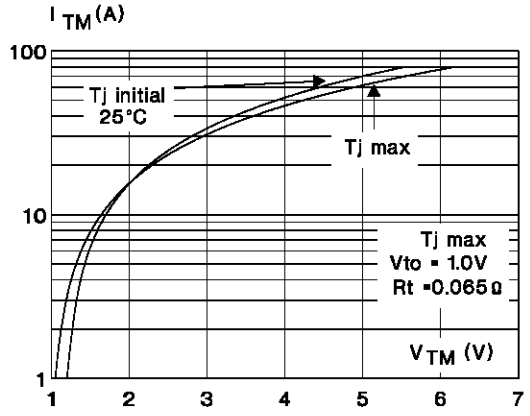
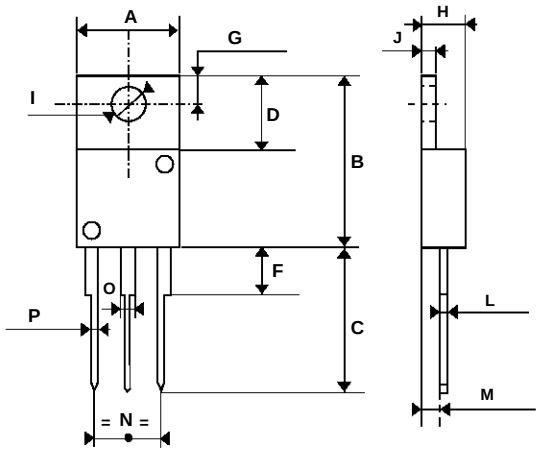


Fig.9 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA

TO220AB Plastic



REF.	DIMENSIONS			
	Millimeters		Inches	
	Min.	Max.	Min.	Max.
A	10.20	10.50	0.401	0.413
B	14.23	15.87	0.560	0.625
C	12.70	14.70	0.500	0.579
D	5.85	6.85	0.230	0.270
F		4.50		0.178
G	2.54	3.00	0.100	0.119
H	4.48	4.82	0.176	0.190
I	3.55	4.00	0.140	0.158
J	1.15	1.39	0.045	0.055
L	0.35	0.65	0.013	0.026
M	2.10	2.70	0.082	0.107
N	4.58	5.58	0.18	0.22
O	0.80	1.20	0.031	0.048
P	0.64	0.96	0.025	0.038

Cooling method : C
Marking : type number
Weight : 2.3 g
Recommended torque value : 0.8 m.N.
Maximum torque value : 1 m.N.

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